

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	50mΩ @ V _{GS} = 10V	18A
	63mΩ @ V _{GS} = 4.5V	16A

Features and Benefits

- Low R_{DS(ON)} – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

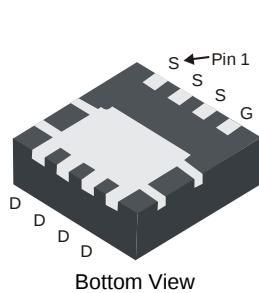
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

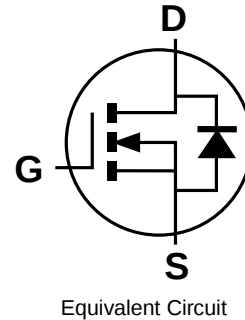
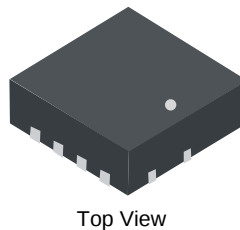
- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.03 grams (Approximate)



POWERDI3333-8

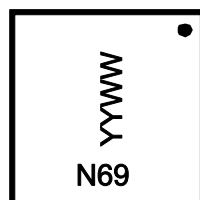


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6069SFG-7	POWERDI3333-8	2,000/Tape & Reel
DMN6069SFG-13	POWERDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N69 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 15 = 2015)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.6 4.5	A
	Steady State	T _C = +25°C T _C = +70°C	I _D	18 14.5	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	25	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2.5	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	12	A
Repetitive Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	7.2	mJ

Thermal Characteristics

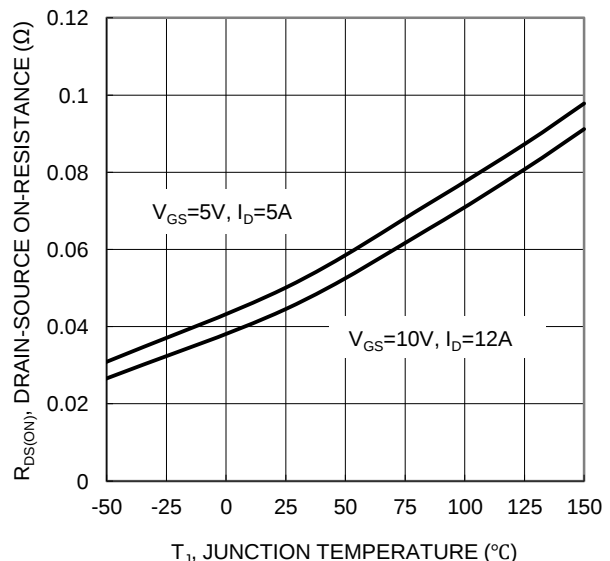
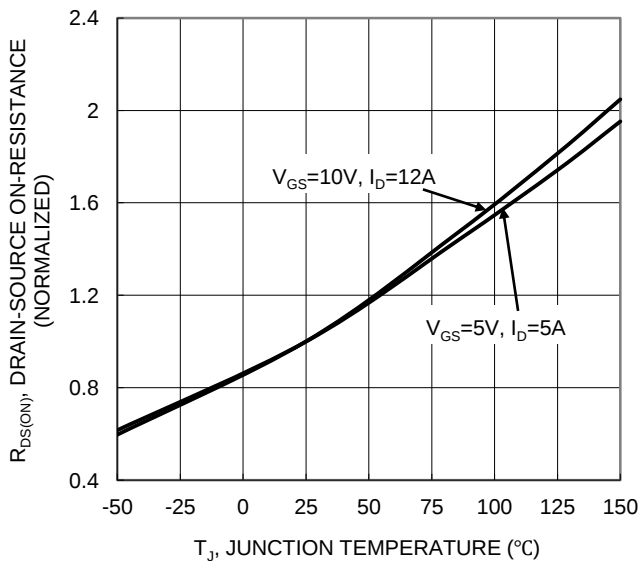
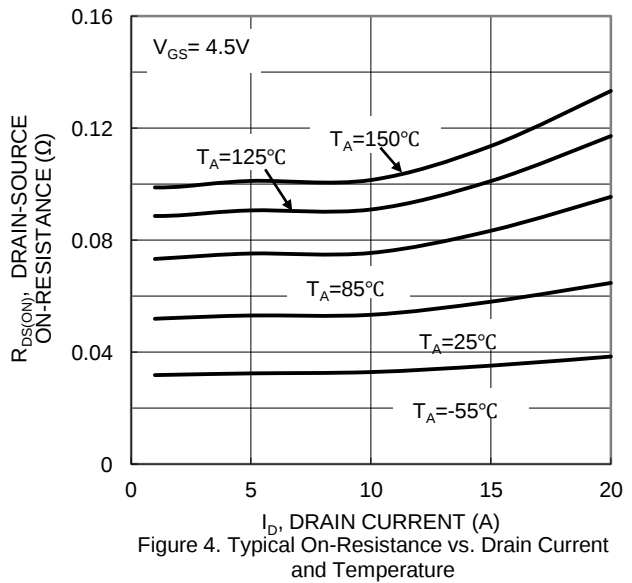
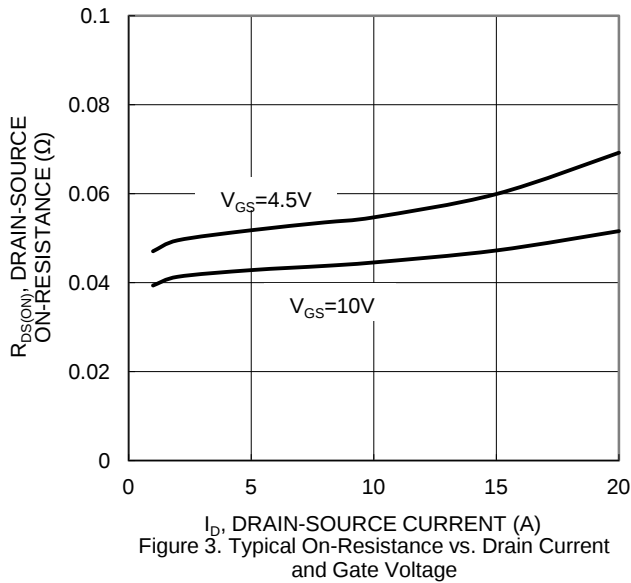
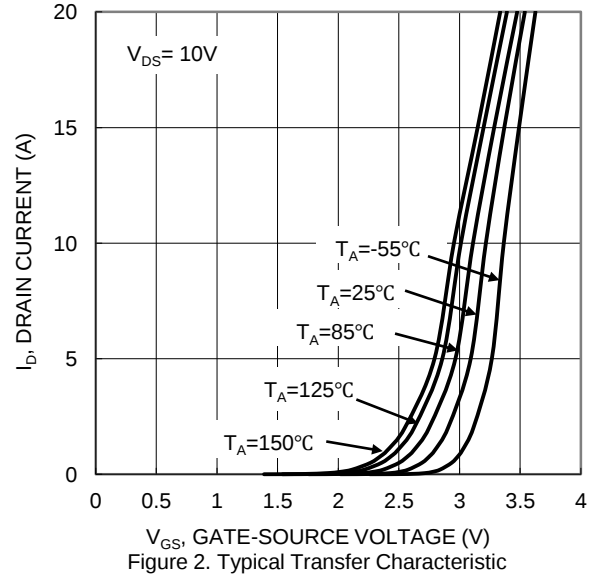
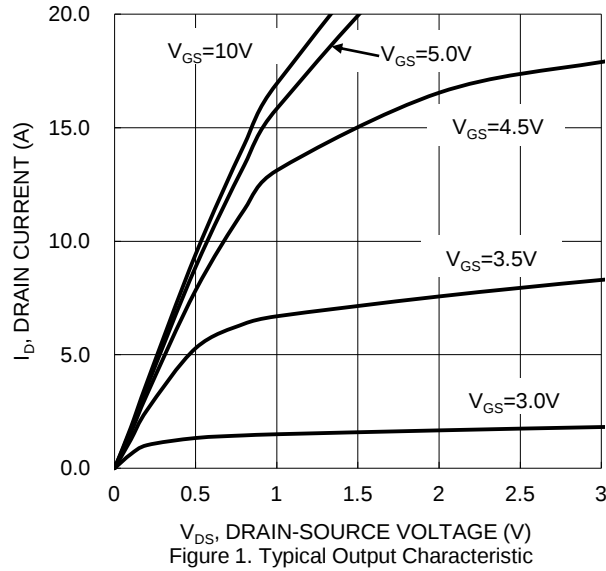
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	0.93	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	134	°C/W
	t < 10s		82	
Total Power Dissipation (Note 6)		P _D	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	53	°C/W
	t < 10s		33	
Thermal Resistance, Junction to Case		R _{θJC}	5	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

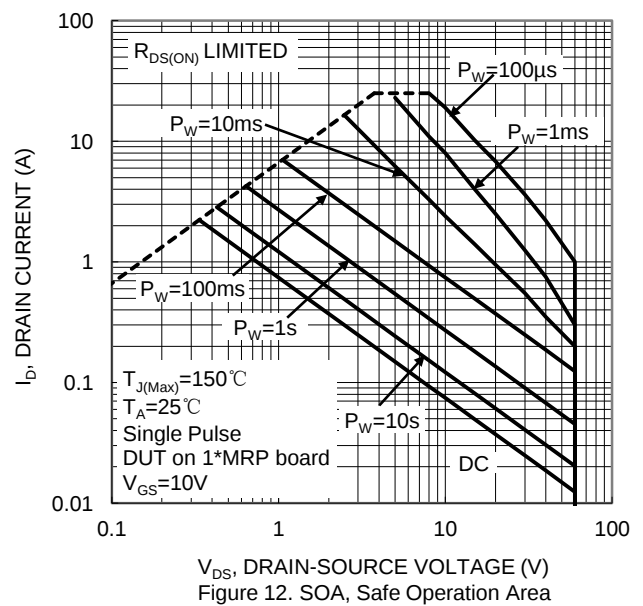
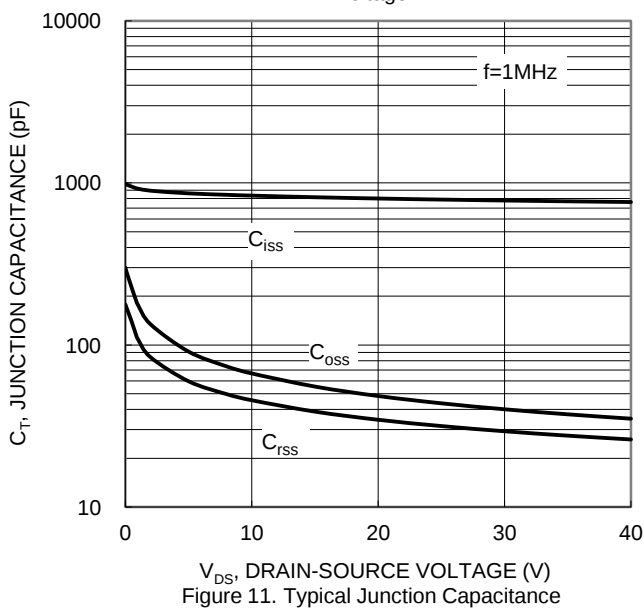
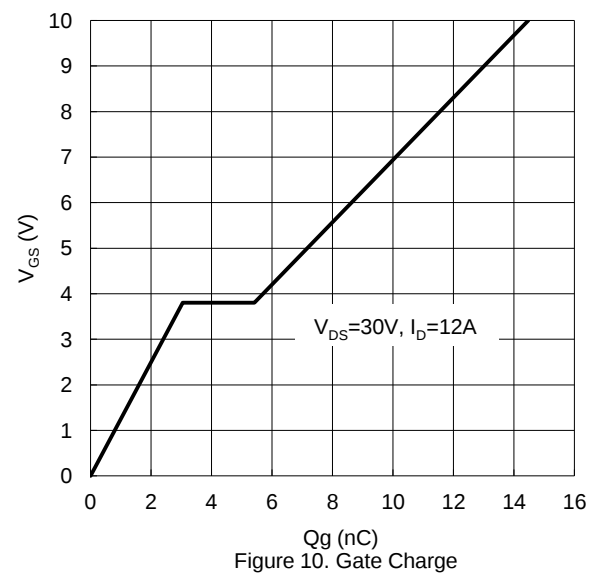
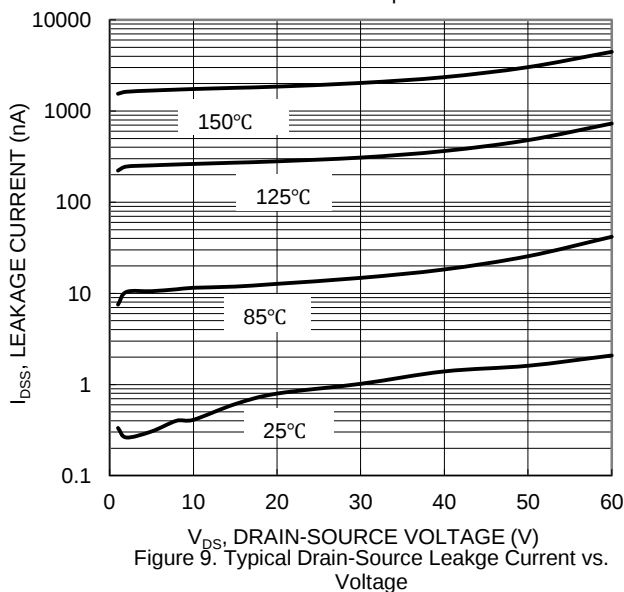
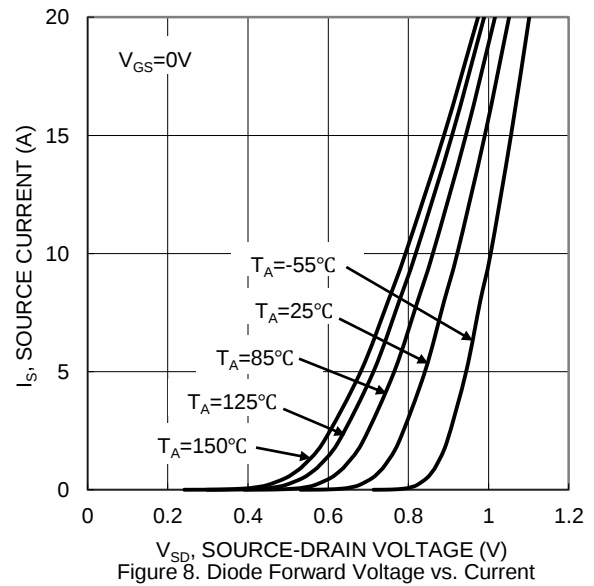
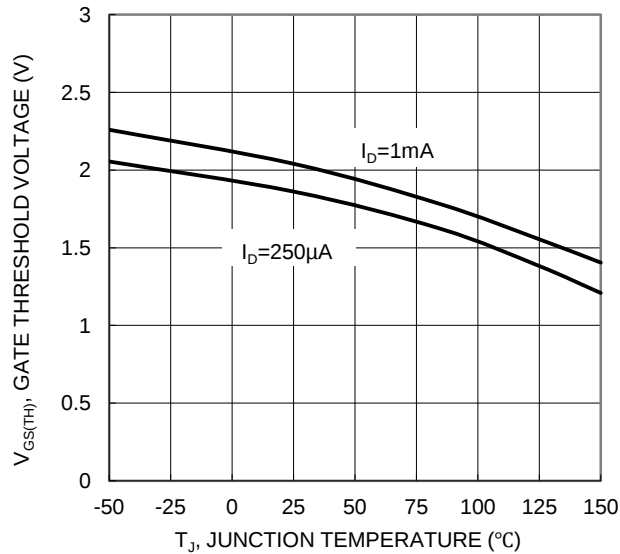
- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics ($T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	1	μA	$V_{DS} = 60V, V_{GS} = 0V$
Zero Gate Voltage Drain Current $T_J = +150^\circ\text{C}$ (Note 9)	I_{DSS}	—	—	100	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	39	50	m Ω	$V_{GS} = 10V, I_D = 4.5A$
		—	47	63		$V_{GS} = 4.5V, I_D = 3A$
Diode Forward Voltage	V_{SD}	—	—	1.1	V	$V_{GS} = 0V, I_S = 2.5A$
On State Drain Current (Note 9)	$I_{D(ON)}$	20	—	—	A	$V_{DS} \geq 5V, V_{GS} = 10V$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{ISS}	—	740	1,480	pF	$V_{DS} = 30V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{OSS}	—	40	80	pF	
Reverse Transfer Capacitance	C_{RSS}	—	28	55	pF	
Gate Resistance	R_g	—	2.2	4	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge ($V_{GS} = 4.5V$)	Q_g	—	6.4	12	nC	$V_{DS} = 30V, I_D = 12A$
Total Gate Charge ($V_{GS} = 10V$)	Q_g	—	14	25	nC	
Gate-Source Charge	Q_{gs}	—	2.8	5.5	nC	
Gate-Drain Charge	Q_{gd}	—	2.3	5	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.6	10	nS	$V_{DS} = 30V, I_D = 12A$ $V_{GS} = 10V, R_G = 6.0\Omega$
Turn-On Rise Time	t_R	—	5.0	10	nS	
Turn-Off Delay Time	$t_{D(OFF)}$	—	12	24	nS	
Turn-Off Fall Time	t_F	—	3.3	10	nS	
Body Diode Reverse Recovery Time	t_{RR}	—	11	22	nS	$I_F = 4.5A, di/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{RR}	—	5.1	10	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.





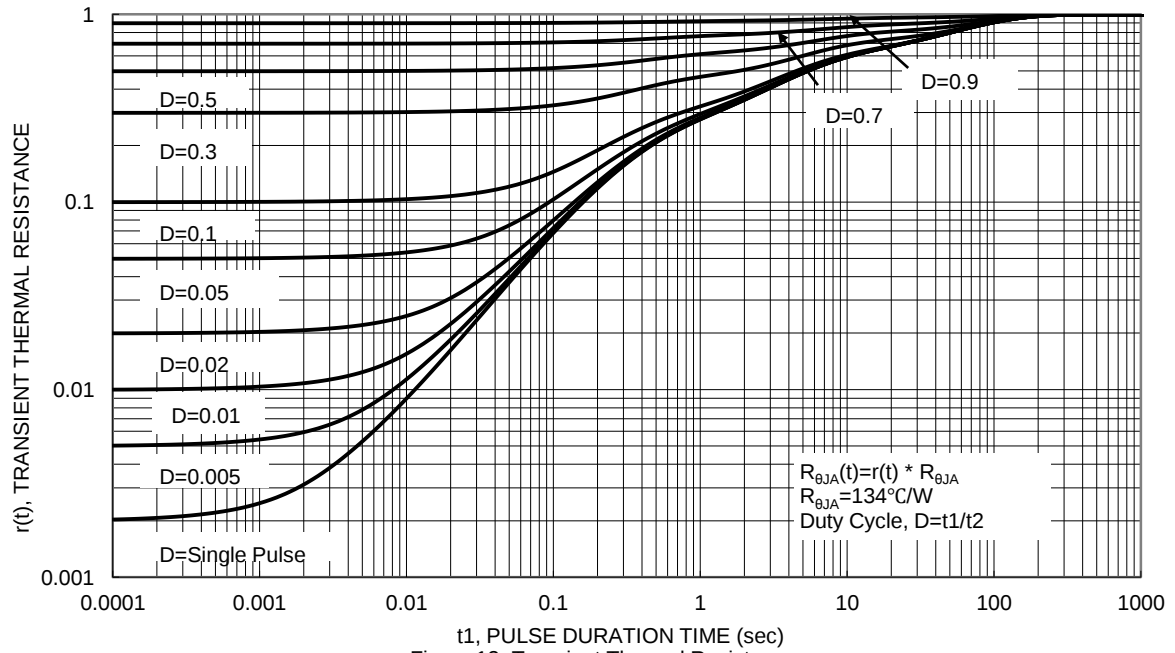
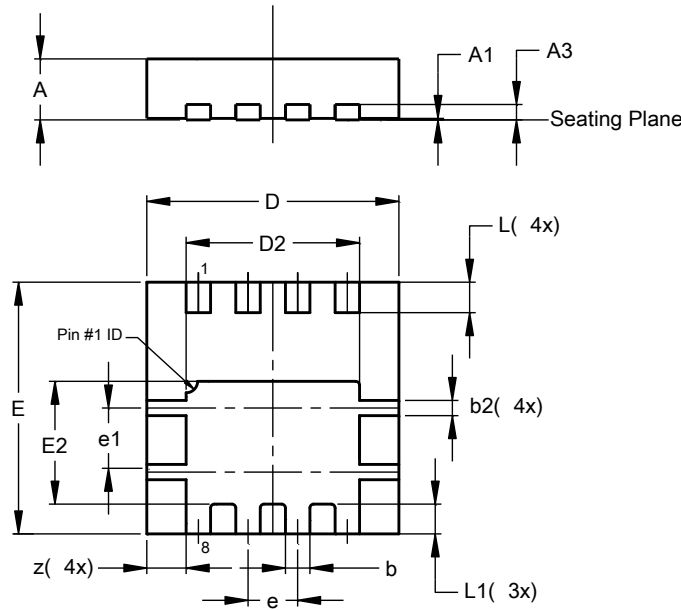


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

POWERDI3333-8

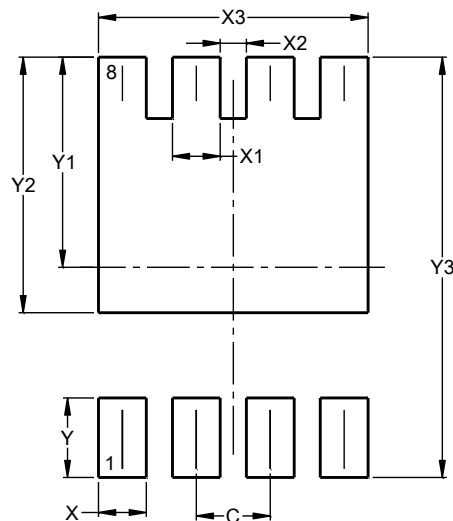


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Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	—	—	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

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Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

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moschip.ru_9